

Ideally, M1 (one finger) and M2 (five fingers) should have same values of channel current since their W and L values are same, but these values are different because for the fingered MOSFETs, the channel current, effective width, and effective resistance of source and drain are functions of nf .

Hence, the channel current value also differs slightly. Refer to the BSIM4.5 manual for detailed expressions. (http://www-device.eecs.berkeley.edu/~bsim3/bsim4_get.html)

How NF Differs from Multiplication Parameter M

'M' stands for multiplicity factor. It means that 'M' identical transistors are in parallel. For example,

```
M1 out in vdd vdd pmos w=10u l=1u m=5
```

indicates that 5 identical transistors are connected in parallel with a total width of 50um.

MOSFET Output Templates

Many MOSFET models produce an output template, consisting of a set of parameters that specify the output of state variables, stored charges, capacitances, parasitic diode current, and capacitor currents. Different MOSFET model levels support different subsets of these output parameters.

For example, if your netlist contains four transistors $m0$, $m1$, $m2$, and $m3$, you can print the parameter values during the transient analysis using the following `.print` statement:

```
.print tran lx3(m1) lx4(m1) lx7(m1) lx8(m1)
```

This command prints the values of V_{ds} , I_{ds} , G_m and G_{ds} to the `*.lis` file

Wildcards are also supported, so you can also use the following which prints the V_{ds} of all transistors:

```
.print tran lx3(m*)
```

[Table 4](#) lists all parameters in the MOSFET output templates, and indicates which model levels support each parameter. See also: [Output Template for](#)

Parameters in HiSIM-HVMOS v.1.2.0 and Higher (level=73) and New Output Templates for PSP and Other Models on page 38.

Table 4 Parameters in MOSFET Output Templates

| Name | Alias | Description | MOSFET Level |
|-------|-------|---|-------------------------------|
| L | LV1 | Channel length (L) (also the effective channel length for all MOSFET models except Levels 54, 57, 69 and 70) | All |
| W | LV2 | Channel width (W) (also the effective channel width for all MOSFET models except Levels 54, 57, 69 and 70) | All |
| AD | LV3 | Area of the drain diode (AD) | All |
| AS | LV4 | Area of the source diode (AS) | All |
| ICVDS | LV5 | Initial condition for the drain-source voltage (VDS) | All |
| ICVGS | LV6 | Initial condition for the gate-source voltage (VGS) | All |
| ICVBS | LV7 | Initial condition for the bulk-source voltage (VBS) | All except 57, 58, 59, 70, 71 |
| ICVES | LV7 | Initial condition for the substrate-source voltage (VES) | 57, 58, 59, 70, 71 |
| – | LV8 | Device polarity: <ul style="list-style-type: none"> ▪ 1 = forward ▪ -1 = reverse (not used after HSPICE release 95.3). | All |
| VTH | LV9 | Threshold voltage (bias dependent) | All |
| VDSAT | LV10 | Saturation voltage (VDSAT) | All |
| PD | LV11 | Drain diode periphery (PD) | All |
| PS | LV12 | Source diode periphery (PS) | All |
| RDS | LV13 | Drain resistance (squares) (RDS) (equals the value of instance parameter nrd/nrs) | All |

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MOSFET Output Templates

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|--|---------------------------|
| RSS | LV14 | Source resistance (squares) (RSS) (equals the value of instance parameter nrd/nrs) | All |
| XQC | LV15 | Charge-sharing coefficient (XQC). | All |
| GDEFF | LV16 | Effective drain conductance (1/RDeff), rgeoMod is not 0 | All |
| GSEFF | LV17 | Effective source conductance (1/RSeff), rgeoMod is not 0 | All |
| CDSAT | LV18 | Drain-bulk saturation current, at -1 V bias. | All |
| CSSAT | LV19 | Source-bulk saturation current, at -1 V bias. | All |
| VDBEFF | LV20 | Effective drain bulk voltage. | All |
| BETAEFF | LV21 | BETA effective | All |
| GAMMAEFF | LV22 | GAMMA effective | All |
| DELTAL | LV23 | ΔL (MOS6 amount of channel length modulation) | 1, 2, 3, 6 |
| UBEFF | LV24 | UB effective | 1, 2, 3, 6 |
| VG | LV25 | VG drive | 1, 2, 3, 6 |
| VFBEFF | LV26 | VFB effective. | All |
| – | LV31 | Drain current tolerance (not used in HSPICE releases after 95.3) | All |
| IDSTOL | LV32 | Source-diode current tolerance | All |
| IDDTOL | LV33 | Drain-diode current tolerance | All |
| COVLGS | LV36 | Gate-source overlap and fringing capacitances | All |
| COVLGD | LV37 | Gate-drain overlap and fringing capacitances | All |
| COVLGB | LV38 | Gate-bulk overlap capacitances | All except 57, 59, 70, 71 |

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|---|-------------------------------|
| COVLGE | LV38 | Gate-substrate overlap capacitances | 57, 59, 70, 71 |
| VBD | L0 | Bulk-drain voltage | All |
| VBS | LX1 | Bulk-source voltage (VBS) | All except 57, 59, 70, 71 |
| VES | LX1 | Substrate-source voltage (VES) | 57, 59, 70, 71 |
| VGS | LX2 | Gate-source voltage (VGS) | All |
| VDS | LX3 | Drain-source voltage (VDS) | All |
| CDO | LX4 | Channel current (IDS) | All |
| CBSO | LX5 | DC source-bulk diode current (CBSO) | All |
| CBDO | LX6 | DC drain-bulk diode current (CBDO) | All |
| GMO | LX7 | DC MOSFET gate transconductance (GMO) ▪ Current is I_{ds} , from drain-to-source, ▪ Voltage is v_{gs} | All |
| GDSO | LX8 | DC drain-source conductance (GDSO) | All |
| GMBSO | LX9 | DC substrate transconductance (GMBSO) | All except 57, 58, 59, 70, 71 |
| GMESO | LX9 | DC substrate transconductance (GMBSO/ GMESO) | 57, 58, 59, 70, 71 |
| GBDO | LX10 | Conductance of the drain diode (GBDO) | All |
| GBSO | LX11 | Conductance of the source diode (GBSO) | All |
| QB | LX12 | Total bulk (body) charge (QB)—Meyer and Charge Conservation | All |
| CQB | LX13 | Bulk (body) charge current (CQB)—Meyer and Charge Conservation | All |

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MOSFET Output Templates

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|--|---------------------------------------|
| QG | LX14 | Total Gate charge (QG)—Meyer and Charge Conservation | All |
| CQG | LX15 | Gate charge current (CQG)—Meyer and Charge Conservation | All |
| QD | LX16 | Total Drain charge (QD) | 49, 53 |
| QD | LX16 | Channel charge (QD)—Meyer and Charge Conservation | All except 49 and 53 |
| CQD | LX17 | Drain charge current (CQD) | 49, 53 |
| CQD | LX17 | Channel charge current (CQD)—Meyer and Charge Conservation | All except 49 and 53 |
| CGGBO | LX18 | $CGGBO = dQg/dVg = CGS + CGD + CGB$ - Meyer and Charge Conservation | All except 54, 57, 59, 60, 70, 71 |
| CGGBO | LX18 | Intrinsic gate capacitance | 54, 57, 59, 60, 66, 70, 71 |
| CGDBO | LX19 | $CGDBO = -dQg/dVd$ - Meyer and Charge Conservation; this cap is the total capacitance, including derivative of charge (dQg/dVd) and overlap capacitance. | All except 54, 57, 59, 60, 66, 70, 71 |
| CGDBO | LX19 | Intrinsic gate-to-drain capacitance | 54, 57, 59, 60, 66, 70, 71 |
| CGSBO | LX20 | $CGSBO = -dQg/dVd$ - Meyer and Charge Conservation | All except 54, 57, 59, 60, 66, 70, 71 |
| CGSBO | LX20 | Intrinsic gate-to-source capacitance | 54, 57, 59, 60, 66, 70, 71 |
| CBGBO | LX21 | $CBGBO = -dQb/dVg$ - Meyer and Charge Conservation | All except 54, 57, 59, 60, 66, 70, 71 |

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|--------|-------|--|---------------------------------------|
| CBGBO | LX21 | Intrinsic bulk-to-gate capacitance | 54, 66 |
| CBGBO | LX21 | Intrinsic floating body-to-gate capacitance | 57, 59, 60, 70, 71 |
| CBDBO | LX22 | CBDBO = $-dQ_b/dV_d$ - Meyer and Charge Conservation | All except 54, 57, 59, 60 |
| CBDBO | LX22 | Intrinsic bulk-to-drain capacitance | 54, 66 |
| CBDBO | LX22 | Intrinsic floating body-to-drain capacitance | 57, 59, 60, 70, 71 |
| CBSBO | LX23 | CBSBO = $-dQ_b/dV_s$ - Meyer and Charge Conservation | All except 54, 57, 59, 60, 66, 70, 71 |
| CBSBO | LX23 | Intrinsic bulk-to-source capacitance | 54, 66 |
| CBSBO | LX23 | Intrinsic floating body-to-source capacitance | 57, 59, 60, 70, 71 |
| QBD | LX24 | Drain-bulk charge (QBD) | All |
| – | LX25 | Drain-bulk charge current (CQBD), (not used in HSPICE releases after 95.3). | All |
| QBS | LX26 | Source-bulk charge (QBS) | All |
| – | LX27 | Source-bulk charge current (CQBS), (not used after HSPICE release 95.3). | All |
| CAP_BS | LX28 | Extrinsic drain to substrate Capacitances—Meyer and Charge Conservation. $CAP_BS = csbox + csesw$ <ul style="list-style-type: none"> ▪ csbox is the substrate-to-source bottom capacitance ▪ csesw is the substrate-to-source sidewall capacitance | 57, 58, 70, 71 |

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MOSFET Output Templates

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|---|---------------------------------------|
| CAP_BS | LX28 | Bias dependent bulk-source capacitance | All except 57, 58, 70, 71 |
| CAP_BD | LX29 | Extrinsic source to substrate Capacitances—Meyer and Charge Conservation. $CAP_BD = cdbox + cdesw$ <ul style="list-style-type: none"> ▪ $cdbox$ is the substrate-to-drain bottom capacitance ▪ $cdesw$ is the substrate-to-drain sidewall capacitance | 57, 58, 70, 71 |
| CAP_BD | LX29 | Bias dependent bulk-drain capacitance | All except 57, 58, 70, 71 |
| CQS | LX31 | Channel-charge current (CQS). | All |
| CDGBO | LX32 | $CDGBO = -dQd/dVg$ - Meyer and Charge Conservation | All except 54, 57, 59, 60, 66, 70 |
| CDGBO | LX32 | Intrinsic drain-to-gate capacitance | 54, 57, 59, 60, 66, 70 |
| CDDBO | LX33 | $CDDBO = dQd/dVd$ - Meyer and Charge Conservation | All except 54, 57, 59, 60, 66, 70, 71 |
| CDDBO | LX33 | Intrinsic drain capacitance | 54, 57, 59, 60, 66, 70, 71 |
| CDSBO | LX34 | $CDSBO = -dQd/dVs$ | All |
| | | Drain-to-source capacitance - Meyer and Charge Conservation | |
| QE | LX35 | Substrate charge (QE)—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| CQE | LX36 | Substrate charge current (CQE)—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|---|---------------------|
| CDEBO | LX37 | CDEBO = $-dQ_d/dV_e$ intrinsic drain-to-substrate capacitance | 57, 59, 70, 71 |
| CBEBO | LX38 | CBEBO = $-dQ_b/dV_e$ intrinsic floating body-to-substrate capacitance | 59, 70, 71 |
| igso | LX38 | Gate-to-Source Current | 54, 69 |
| CEEBO | LX39 | CEEBO = dQ_e/dV_e intrinsic substrate capacitance | 59, 70, 71 |
| igdo | LX39 | Gate-to-Drain Current | 54, 69 |
| CEGBO | LX40 | CEGBO = $-dQ_e/dV_g$ intrinsic substrate-to-gate capacitance | 57, 59, 70, 71 |
| CEDBO | LX41 | CEDBO = $-dQ_e/dV_d$ intrinsic substrate-to-drain capacitance | 57, 59, 70, 71 |
| CESBO | LX42 | CESBO = $-dQ_e/dV_s$ intrinsic substrate-to-source capacitance | 57, 59, 70, 71 |
| VBSI | LX43 | Body-source voltage (VBS)—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| ICH | LX44 | Channel current—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| IBJT | LX45 | Parasitic BJT collector current—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| III | LX46 | Impact ionization current—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| IGIDL | LX47 | GIDL current—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| ITUN | LX48 | Tunneling current—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| Qbacko | LX49 | Back gate charge | 57, 59, 70, 71 |

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Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|---|---------------------|
| lbp | LX50 | Body contact current | 57, 59, 70, 71 |
| Sft | LX51 | Value of the temperature node with shmod=1 | 57, 59, 70, 71 |
| VBFLOAT | LX52 | Internal body node voltage, if you do not specify the terminal | 57, 59, 70, 71 |
| Rbp | LX53 | Combination of rbody and rhalo | 57, 59, 70, 71 |
| IGB | LX54 | Gate tunneling current | 57, 59, 70, 71 |
| QSRCO | LX55 | Total Source charge (Charge Conservation: $QS = -(QG + QD + QB)$) | 49, 53 |
| QSRCO | LX55 | Total Source charge (Charge Conservation: $QS = -(QG + QD + QB + QE)$) | 57, 59, 70, 71 |
| CQs | LX56 | Source charge current | 57, 59, 70, 71 |
| CGEBO | LX57 | $CGEBO = -dQg/dVe$ intrinsic gate-to-substrate capacitance | 57, 59, 70, 71 |
| CSSBO | LX58 | $CSSBO = dQs/dVs$ intrinsic source capacitance | 57, 59, 70, 71 |
| CSGBO | LX59 | $CSGBO = -dQs/dVg$ intrinsic source-to-gate capacitance | 57, 59, 70, 71 |
| CSDBO | LX60 | $CSDBO = -dQs/dVd$ intrinsic source-to-drain capacitance | 57, 59, 70, 71 |
| CSEBO | LX61 | $CSEBO = -dQs/dVe$ intrinsic source-to-substrate capacitance | 57, 59, 70, 71 |
| weff | LX62 | Effective channel width | 54, 57, 66, 69, 70 |
| leff | LX63 | Effective channel length | 54, 57, 66, 69, 70 |
| weffcv | LX64 | Effective channel width for CV | 54, 66, 69 |
| leffcv | LX65 | Effective channel length for CV | 54, 66, 69 |

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|--|--------------------------------|
| igbo | LX66 | Gate-to-Substrate Current ($I_{gb} = I_{gbacc} + I_{gbinv}$) | 54, 69 |
| igcso | LX67 | Source Partition of I_{gc} | 54, 69 |
| igcdo | LX68 | Drain Partition of I_{gc} | 54, 69 |
| iimi | LX69 | Impact ionization current | 54, 69 |
| igidlo | LX70 | Gate-induced drain leakage current | 54, 69 |
| igdt | LX71 | Gate Dielectric Tunneling Current ($I_g = I_{gs} + I_{gd} + I_{gcs} + I_{gcd} + I_{gb}$) | 54, 69 |
| igc | LX72 | Gate-to-Channel Current at zero V_{ds} | 54, 69 |
| igbacc | LX73 | Determined by ECB (Electron tunneling from the Conduction Band); significant in the accumulation | 54 |
| igbinv | LX74 | Determined by EVB (Electron tunneling from the Valence Band); significant in the inversion | 54 |
| vfbsd | LX75 | Flat-band Voltage between the Gate and S/D diffusions | 54, 66 |
| vgse | LX76 | Effective Gate-to-Source Voltage | 54, 66 |
| vox | LX77 | Voltage Across Oxide | 54, 66 |
| rdv | LX78 | Asymmetric and Bias-Dependent Source Resistance, ($r_{dsMod} = 1$) | 54, 66 |
| rsv | LX79 | Asymmetric and Bias-Dependent Drain Resistance, ($r_{dsMod} = 1$) | 54, 66 |
| cap_bsz | LX80 | Zero voltage bias bulk-source capacitance | 54, 66 |
| cap_bdz | LX81 | Zero voltage bias bulk-drain capacitance | 54, 66 |
| CGGBM | LX82 | Total gate capacitance (including intrinsic), and all overlap and fringing components | 54, 57, 59, 60, 66, 70, 69, 71 |

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|--|--------------------------------|
| CGDBM | LX83 | Total gate-to-drain capacitance (including intrinsic), and overlap and fringing components | 54, 57, 59, 60, 66, 69, 70, 71 |
| CGSBM | LX84 | Total gate-to-source capacitance (including intrinsic), and overlap and fringing components | 54, 57, 59, 60, 66, 69, 70, 71 |
| CDDBM | LX85 | Total drain capacitance (including intrinsic), overlap and fringing components, and junction capacitance | 54, 57, 59, 60, 66, 69, 70, 71 |
| CDSBM | LX86 | Total drain-to-source capacitance | 54, 57, 60, 66, 69, 70, 71 |
| CDGBM | LX87 | Total drain-to-gate capacitance (including intrinsic), and overlap and fringing components | 54, 57, 59, 60, 66, 69, 70, 71 |
| CBGBM | LX88 | Total bulk-to-gate (floating body-to-gate) capacitance, including intrinsic and overlap components | 54, 57, 59, 60, 66, 70, 71 |
| CBDBM | LX89 | Total bulk-to-drain capacitance (including intrinsic), and junction capacitance | 54, 66 |
| CBDBM | LX89 | Total floating body-to-drain capacitance (including intrinsic), and junction capacitance. | 57, 59, 60, 70, 71 |
| CBSBM | LX90 | Total bulk-to-source capacitance (including intrinsic), and junction capacitance | 54, 66 |
| CBSBM | LX90 | Total floating body-to-source capacitance (including intrinsic), and junction capacitance. | 57, 59, 60, 70, 71 |
| CAPFG | LX91 | Fringing capacitance | 54, 66 |
| CDEBM | LX92 | Total drain-to-substrate capacitance (including intrinsic), and junction capacitance. | 57, 59, 60, 70, 71 |
| CSGBM | LX93 | Total source-to-gate capacitance (including intrinsic), and overlap and fringing components. | 57, 59, 60, 70, 71 |

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|---|---------------------|
| CSSBM | LX94 | Total source capacitance (including intrinsic), overlap and fringing components, and junction capacitance. | 57, 59, 60, 70, 71 |
| CSEBM | LX95 | Total source-to-substrate capacitance (including intrinsic), and junction capacitance. | 57, 59, 60, 70, 71 |
| CEEBM | LX96 | Total substrate capacitance (including intrinsic), overlap and fringing components, and junction capacitance. | 57, 59, 60, 70, 71 |
| QGI | LX97 | Intrinsic Gate charge | 49, 53 |
| QSI | LX98 | Intrinsic Source charge | 49, 53 |
| QDI | LX99 | Intrinsic Drain charge | 49, 53 |
| QBI | LX100 | Intrinsic Bulk charge (Charge Conservation: $QBI = -(QGI + QSI + QDI)$) | 49, 53 |
| CDDBI | LX101 | Intrinsic drain capacitance; only includes derivative of charge | 49, 53 |
| CBDBI | LX102 | Intrinsic bulk-to-drain capacitance; only includes derivative of charge | 49, 53 |
| CBSBI | LX103 | Intrinsic bulk-to-source capacitance; only includes derivative of charge | 49, 53 |
| VBDI | LX109 | Body-drain voltage(VBD)—Meyer and Charge Conservation | 57, 58, 59, 70, 71 |
| IGISLO | LX110 | Gate-induced source leakage current | 54 |
| GRII | LX118 | Intrinsic channel reflected gate conductance | 54 |
| GRGELTD | LX119 | Gate electrode conductance | 54 |
| bs1 | LX120 | Bulk to source diffusion current | 57, 59, 60 |
| lbd1 | LX121 | Bulk to drain diffusion current | 57, 59, 60 |

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Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|-------------|--------------|--|---------------------|
| lbs2 | LX122 | Bulk to source recombination/trap-assisted tunneling current | 57, 59, 60 |
| lbd2 | LX123 | Bulk to drain recombination/trap-assisted tunneling current | 57, 59, 60 |
| lbs3 | LX124 | Bulk to source recombination current in neutral body | 57, 59, 60 |
| lbd3 | LX125 | Bulk to drain recombination current in neutral body | 57, 59, 60 |
| lbs4 | LX126 | Bulk to source reversed bias tunneling leakage current | 57, 59, 60 |
| lbd4 | LX127 | Bulk to drain reversed bias tunneling leakage current | 57, 59, 60 |
| b4_sca | LX128 | sca for WPE effect | 54 |
| b4_scb | LX129 | scb for WPE effect | 54 |
| b4_scc | LX130 | scc for WPE effect | 54 |
| b4_sc | LX131 | sc for WPE effect | 54 |
| Ueff | LX132 | Effective mobility at the specified analysis temperature | 66 |
| VGB | LX133 | Gate to bulk voltage | All |
| VDG | LX134 | Drain to gate voltage | All |
| mult | LX135 | Prints value of multiplier (M) for a specified MOSFET | All |
| b4_sa | LX136 | sa for STI or LOD-induced mechanical stress-effects | 54 |
| b4_sb | LX137 | sb for STI or LOD-induced mechanical stress-effects | 54 |

Table 4 Parameters in MOSFET Output Templates (Continued)

| Name | Alias | Description | MOSFET Level |
|----------|-------------|---|--------------|
| b4_sd | LX138 | sd for STI or LOD-induced mechanical stress-effects | 54 |
| b4_nf | LX139 | nf for STI or LOD-induced mechanical stress-effects | 54 |
| b4_saeff | LX140 | saeff for STI or LOD-induced mechanical stress-effects | 54 |
| b4_sbeff | LX141 | sbeff for STI or LOD-induced mechanical stress-effects | 54 |
| ivth(m*) | LX142 (m*) | New vth output, based on the monotony Id/Vgs curve obtained through .OPTION IVTH; ivthn and ivthp support NMOS and PMOS, respectively | 54, 69, 70 |
| soiq0 | LX143 (bqi) | Initial floating body charge at t=0 for BQI. If it is not given, 1e35 will be printed. For tran analysis (t>0), the floating body charge will be printed. This parameter only supports BQI. | 57, 60, 70 |

Additional MOSFET Output templates include:

- [Output Template for Parameters in HiSIM-HVMOS v.1.2.0 and Higher \(level=73\)](#)
- [New Output Templates for PSP and Other Models](#)

Output Template for Parameters in HiSIM-HVMOS v.1.2.0 and Higher (level=73)

HSPICE supports parameter output templates for HiSIM-HV beginning with version 1.2.0 model (version=1.20 level=73).

Table 5 Output Templates for HiSIM LDMOS/HVMOS Model -1.2.0

| Name | Alias | Description |
|------|-------|--------------------|
| L | LX291 | Channel Length (L) |